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Single Phase Fast Recovery Bridge (Power Modules), 61 A



PRIMARY CHARACTERISTICS				
V _{RRM}	600 V			
Ι _Ο	61 A			
t _{rr}	170 ns			
Туре	Modules - Bridge, Fast			
Package	SOT-227			
Circuit configuration	Single phase bridge			

FEATURES

- Fast recovery time characteristic
- Electrically isolated base plate
- Simplified mechanical designs, rapid assembly
- Excellent power/volume ratio
- Designed and qualified for industrial and consumer level
- UL approved file E78996
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
Io		61	А			
	T _C	57	°C			
I _{FSM}	50 Hz	300	٨			
	60 Hz	310	A			
l ² t	50 Hz	442	A ² s			
	60 Hz	402	A-S			
V _{RRM}		600	V			
TJ		-55 to +150	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS						
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J MAXIMUM mA		
SA61BA60	60	600	700	10		



COMPLIANT



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FORWARD CONDUCTION							
PARAMETER	SYMBOL		TEST CONDITION	VALUES	UNITS		
Maximum DC output current		Resistive or inductive load		61	А		
at case temperature	lo				57	°C	
		t = 10 ms	No voltage		300		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		310	A	
non-repetitive forward current	I _{FSM}	t = 10 ms	100 % V _{RRM}		250		
		t = 8.3 ms	reapplied	Initial T _J =	260		
	l ² t	t = 10 ms	No voltage	T _J maximum	442	A ² s	
Maximum I ² t for fusing		t = 8.3 ms	reapplied		402		
		t = 10 ms	100 % V _{RRM}		313		
		t = 8.3 ms	reapplied		284		
Maximum I²√t for fusing	l²√t	I^2t for time t_x = $I_2 \sqrt{t} \; x \; \sqrt{t_x}; 0.1 \leq t_x \leq 10 \; \text{ms}, V_{\text{RRM}}$ = 0 V			4.4	kA²√s	
Value of threshold voltage	V _{F(TO)}	T _J maximum			0.914	V	
Forward slope resistance	r _t				10.5	mΩ	
Maximum forward voltage drop	V_{FM}	$T_J = 25 \text{ °C}, I_{FN}$	C, $I_{FM} = 30 A_{pk}$		1.33		
Maximum forward voltage drop		$T_{\rm J} = T_{\rm J} \text{ maximum, } I_{\rm FM} = 30 \text{ A}_{\rm pk} \qquad t_{\rm p} = 400 \mu\text{s}$		1.23	V		
RMS isolation voltage base plate	VISOL	f = 50 Hz, t = 1 s		3000			

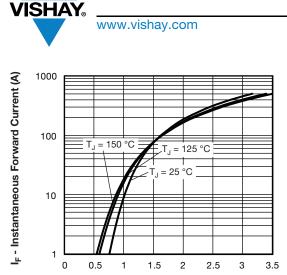
RECOVERY CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Payoraa raaayaay tima tunical	+	$T_J = 25 \ ^\circ C, I_F = 20 \ A, V_R = 30 \ V, dI_F/dt = 100 \ A/\mu s$	170	20		
Reverse recovery time, typical	t _{rr}	$T_J = 125 \ ^\circ C$, $I_F = 20 \ A$, $V_R = 30 \ V$, $dI_F/dt = 100 \ A/\mu s$	250	ns	· •	
Reverse recovery current, typical	I _{rr}	$\begin{array}{l} T_{J} = 25 \ ^{\circ}C, \ I_{F} = 20 \ A, \ V_{R} = 30 \ V, \\ dI_{F}/dt = 100 \ A/\mu s \end{array}$	10.5	A	٨	I _{FM} t
		$T_J = 125 \text{ °C}, I_F = 20 \text{ A}, V_R = 30 \text{ V}, $ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	16			
Reverse recovery charge, typical	0	$T_J = 25 \ ^\circ C$, $I_F = 20 \ A$, $V_R = 30 \ V$, $dI_F/dt = 100 \ A/\mu s$	900	nC		
neverse recovery charge, typical	Q _{rr}	$\begin{array}{l} T_J = 125 \ ^\circ C, \ I_F = 20 \ A, \ V_R = 30 \ V, \\ dI_F/dt = 100 \ A/\mu s \end{array}$	1970			
Snap factor, typical	S	T _J = 25 °C	0.6	-		
Junction capacitance, typical	CT	V _R = 600 V	67	pF		

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	T _J , T _{Stg}		- 55	-	150	°C
Thermal resistance junction to case, per diode	D		-	-	1.2	
Thermal resistance junction to case, per module	R _{thJC}		-	-	0.30	°C/W
Thermal resistance case to heatsink	R _{thCS}	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				S	OT-227	

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V_{FM} - Forward Voltage Drop (V)

Fig. 1 - Typical Forward Voltage Drop Characteristics

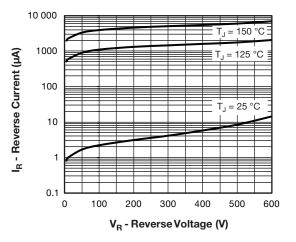


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

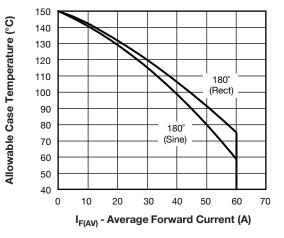


Fig. 5 - Forward Power Loss Characteristics

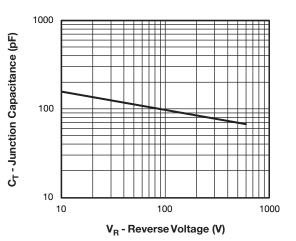


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

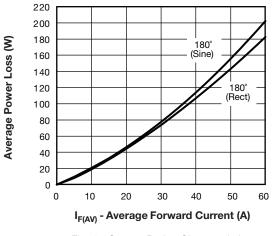


Fig. 4 - Current Rating Characteristics

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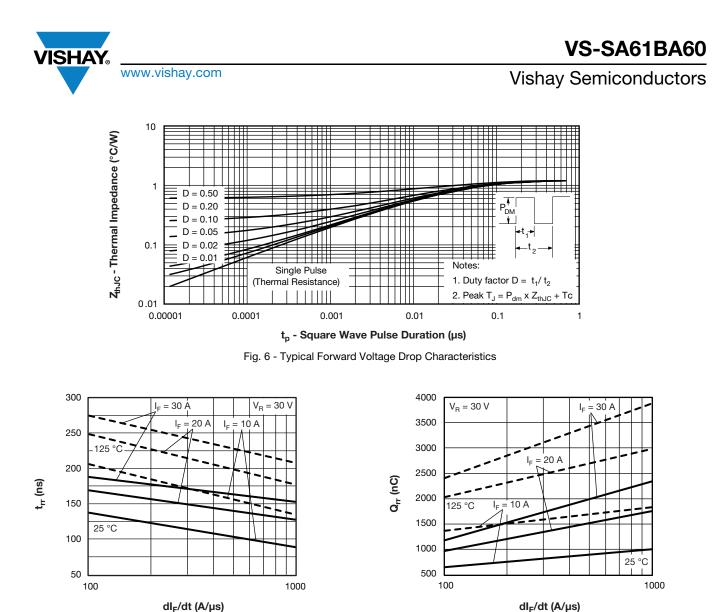


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Fig. 8 - Typical Stored Charge vs. dl_F/dt

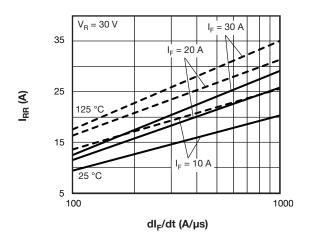


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt

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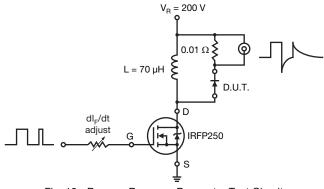
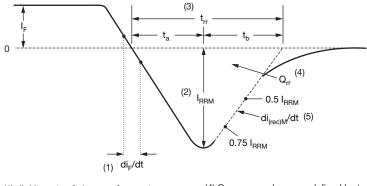


Fig. 10 - Reverse Recovery Parameter Test Circuit



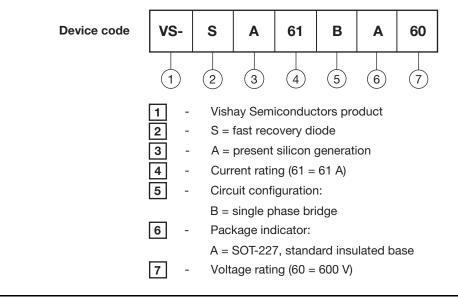
- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) ${\rm Q}_{\rm rr}$ - area under curve defined by ${\rm t}_{\rm rr}$ and ${\rm I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

- (5) di_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}
- Fig. 11 Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE



VS-SA61BA60





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CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Single phase bridge	В	(AC) 4 0 4 0 4 0 4 0 4 0 4 0 4 0 4 0 4 0 4				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95423					
Packaging information	www.vishay.com/doc?95425				

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SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

• Controlling dimension: millimeter



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